

General Description

The 844003-01 is a 3 differential output LVDS Synthesizer designed to generate Ethernet reference clock frequencies. Using a 19.53125MHz or 25MHz, 18pF parallel resonant crystal, the following frequencies can be generated based on the settings of 4 frequency select pins (DIV_SELA[1:0], DIV_SELB[1:0]): 625MHz, 312.5MHz, 156.25MHz, and 125MHz. The 844003-01 has 2 output banks, Bank A with 1 differential LVDS output pair and Bank B with 2 differential LVDS output pairs.

The two banks have their own dedicated frequency select pins and can be independently set for the frequencies mentioned above. The 844003-01 uses IDT's 3rd generation low phase noise VCO technology and can achieve 1ps or lower typical rms phase jitter, easily meeting Ethernet jitter requirements. The 844003-01 is packaged in a small 24-pin TSSOP package.

Features

- Three differential LVDS output pairs on two banks, Bank A with one LVDS pair and Bank B with two LVDS output pairs
- Using a 19.53125MHz or 25MHz crystal, the two output banks can be independently set for 625MHz, 312.5MHz, 156.25MHz or 125MHz
- Selectable crystal oscillator interface or LVCMOS/LVTTL single-ended input
- VCO range: 490MHz - 680MHz
- RMS phase jitter @ 156.25MHz (1.875MHz – 20MHz): 0.56ps (typical)
- Full 3.3V supply mode
- 0°C to 70°C ambient operating temperature
- Available in lead-free (RoHS 6) package

Pin Assignment

| | | | |
|-----------|----|----|-----------|
| DIV_SELB0 | 1 | 24 | DIV_SELB1 |
| VCO_SEL | 2 | 23 | VDDO_B |
| MR | 3 | 22 | QB0 |
| VDDO_A | 4 | 21 | nQB0 |
| QA0 | 5 | 20 | QB1 |
| nQA0 | 6 | 19 | nQB1 |
| OEB | 7 | 18 | XTAL_SEL |
| OEA | 8 | 17 | REF_CLK |
| FB_DIV | 9 | 16 | XTAL_IN |
| VDDA | 10 | 15 | XTAL_OUT |
| VDD | 11 | 14 | GND |
| DIV_SELA0 | 12 | 13 | DIV_SELA1 |

844003-01

24-Lead TSSOP, E-Pad
4.40mm x 7.8mm x 0.925mm
package body
G Package
Top View

Block Diagram

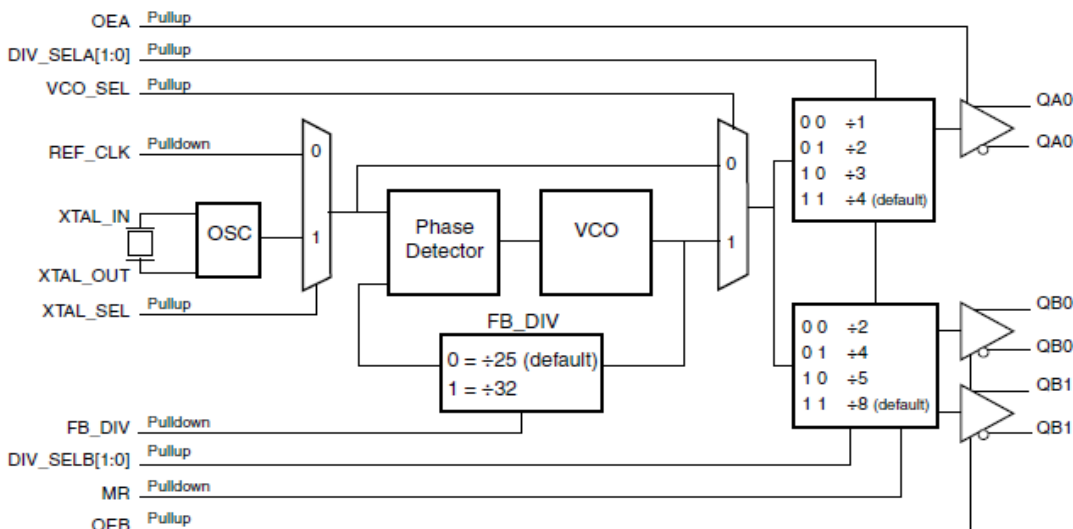


Table 1. Pin Descriptions

| Number | Name | Type | | Description |
|--------|----------------------|--------|----------|--|
| 1, 24 | DIV_SELB0, DIV_SELB1 | Input | Pullup | Division select pin for Bank B. Default = HIGH. LVCMOS/LVTTL interface levels. See Table 3B. |
| 2 | VCO_SEL | Input | Pullup | VCO select pin. When Low, the PLL is bypassed and the crystal reference or REF_CLK (depending on XTAL_SEL setting) are passed directly to the output dividers. Has an internal pullup resistor so the PLL is not bypassed by default. LVCMOS/LVTTL interface levels. |
| 3 | MR | Input | Pulldown | Active HIGH Master Reset. When logic HIGH, the internal dividers are reset causing the true outputs Qx to go low and the inverted outputs nQx to go high. When logic LOW, the internal dividers and the outputs are enabled. Has an internal pulldown resistor so the power-up default state of outputs and dividers are enabled. LVCMOS/LVTTL interface levels. |
| 4 | V _{DDO_A} | Power | | Output supply pin for Bank A outputs. |
| 5, 6 | QA0, nQA0 | Output | | Differential output pair. LVDS interface levels. |
| 7 | OEB | Input | Pullup | Output enable Bank B. Active High outputs are enable. When logic HIGH, the output pairs on Bank B are enabled. When logic LOW, the output pairs are in a high impedance state. Has an internal pullup resistor so the default power-up state of outputs are enabled. LVCMOS/LVTTL interface levels. See Table 3E. |
| 8 | OEA | Input | Pullup | Output enable Bank A. Active High output enable. When logic HIGH, the output pair in Bank A is enabled. When logic LOW, the output pair is in a high impedance state. Has an internal pullup resistor so the default power-up state of output is enabled. LVCMOS/LVTTL interface levels. See Table 3D. |
| 9 | FB_DIV | Input | Pulldown | Feedback divide select. When Low (default), the feedback divider is set for ÷25. When HIGH, the feedback divider is set for ÷32. See Table 3C. LVCMOS/LVTTL interface levels. |
| 10 | V _{DDA} | Power | | Analog supply pin. |
| 11 | V _{DD} | Power | | Core supply pin. |
| 12, 13 | DIV_SELA0, DIV_SELA1 | Input | Pullup | Division select pin for Bank A. Default = HIGH. See Table 3A. LVCMOS/LVTTL interface levels. |
| 14 | GND | Power | | Power supply ground. |
| 15, 16 | XTAL_OUT, XTAL_IN | Input | | Parallel resonant crystal interface. XTAL_OUT is the output, XTAL_IN is the input. XTAL_IN is also the overdrive pin if you want to overdrive the crystal circuit with a single-ended reference clock. |
| 17 | REF_CLK | Input | Pulldown | Single-ended reference clock input. Has an internal pulldown resistor to pull to low state by default. Can leave floating if using the crystal interface. LVCMOS/LVTTL interface levels. |
| 18 | XTAL_SEL | Input | Pullup | Crystal select pin. Selects between the single-ended REF_CLK or crystal interface. Has an internal pullup resistor so the crystal interface is selected by default. LVCMOS/LVTTL interface levels. |
| 19, 20 | nQB1, QB1 | Output | | Differential output pair. LVDS interface levels. |
| 21, 22 | nQB0, QB0 | Output | | Differential output pair. LVDS interface levels. |
| 23 | V _{DDO_B} | Power | | Output supply pin for Bank B outputs. |

NOTE: *Pullup* and *Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

Table 2. Pin Characteristics

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------------|-------------------------|-----------------|---------|---------|---------|-------|
| C _{IN} | Input Capacitance | | | 4 | | pF |
| R _{PULLUP} | Input Pullup Resistor | | | 51 | | kΩ |
| R _{PULLDOWN} | Input Pulldown Resistor | | | 51 | | kΩ |

Function Tables

Table 3A. Output Bank A Configuration Select Function Table

| Inputs | | Outputs |
|-----------|-----------|--------------|
| DIV_SELA1 | DIV_SELA0 | QA0/ nQA0 |
| 0 | 0 | ÷1 |
| 0 | 1 | ÷2 |
| 1 | 0 | ÷3 |
| 1 | 1 | ÷4 (default) |

Table 3B. Output Bank B Configuration Select Function Table

| Inputs | | Outputs |
|-----------|-----------|-------------------|
| DIV_SELB1 | DIV_SELB0 | QB[0:1]/ nQB[0:1] |
| 0 | 0 | ÷2 |
| 0 | 1 | ÷4 |
| 1 | 0 | ÷5 |
| 1 | 1 | ÷8 (default) |

Table 3C. Feedback Divider Configuration Select Function Table

| Input | |
|--------|-----------------|
| FB_DIV | Feedback Divide |
| 0 | ÷25 (default) |
| 1 | ÷32 |

Table 3D. OEA Select Function Table

| Input | Outputs |
|-------|------------------|
| OEA | QA0/ nQA0 |
| 0 | High Impedance |
| 1 | Active (default) |

Table 3E. OEB Select Function Table

| Input | Outputs |
|-------|-------------------|
| OEB | QB[0:1]/ nQB[0:1] |
| 0 | High Impedance |
| 1 | Active (default) |

Table 3F. Bank A Frequency Table

| Inputs | | | | Feedback Divider | Bank A Output Divider | M/N Multiplication Factor | QA0/ nQA0 Output Frequency (MHz) |
|-------------------------|--------|-----------|-----------|------------------|-----------------------|---------------------------|----------------------------------|
| Crystal Frequency (MHz) | FB_DIV | DIV_SELA1 | DIV_SELA0 | | | | |
| 25 | 0 | 0 | 0 | 25 | 1 | 25 | 625 |
| 25 | 0 | 0 | 1 | 25 | 2 | 12.5 | 312.5 |
| 20 | 0 | 0 | 1 | 25 | 2 | 12.5 | 250 |
| 22.5 | 0 | 1 | 0 | 25 | 3 | 8.333 | 187.5 |
| 25 | 0 | 1 | 1 | 25 | 4 | 6.25 | 156.25 |
| 24 | 0 | 1 | 1 | 25 | 4 | 6.25 | 150 |
| 20 | 0 | 1 | 1 | 25 | 4 | 6.25 | 125 |
| 19.44 | 1 | 0 | 0 | 32 | 1 | 32 | 622.08 |
| 19.44 | 1 | 0 | 1 | 32 | 2 | 16 | 311.04 |
| 15.625 | 1 | 0 | 1 | 32 | 2 | 16 | 250 |
| 18.75 | 1 | 1 | 0 | 32 | 3 | 10.667 | 200 |
| 19.44 | 1 | 1 | 1 | 32 | 4 | 8 | 155.52 |
| 18.75 | 1 | 1 | 1 | 32 | 4 | 8 | 150 |
| 15.625 | 1 | 1 | 1 | 32 | 4 | 8 | 125 |

Table 3G. Bank B Frequency Table

| Inputs | | | | Feedback Divider | Bank B Output Divider | M/N Multiplication Factor | QBx/ nQBx Output Frequency (MHz) |
|-------------------------|--------|-----------|-----------|------------------|-----------------------|---------------------------|----------------------------------|
| Crystal Frequency (MHz) | FB_DIV | DIV_SELB1 | DIV_SELB0 | | | | |
| 25 | 0 | 0 | 0 | 25 | 2 | 12.5 | 312.5 |
| 20 | 0 | 0 | 0 | 25 | 2 | 12.5 | 250 |
| 25 | 0 | 0 | 1 | 25 | 4 | 6.25 | 156.25 |
| 24 | 0 | 0 | 1 | 25 | 4 | 6.25 | 150 |
| 20 | 0 | 0 | 1 | 25 | 4 | 6.25 | 125 |
| 25 | 0 | 1 | 0 | 25 | 5 | 5 | 125 |
| 25 | 0 | 1 | 1 | 25 | 8 | 3.125 | 78.125 |
| 24 | 0 | 1 | 1 | 25 | 8 | 3.125 | 75 |
| 20 | 0 | 1 | 1 | 25 | 8 | 3.125 | 62.5 |
| 19.44 | 1 | 0 | 0 | 32 | 2 | 16 | 311.04 |
| 15.625 | 1 | 0 | 0 | 32 | 2 | 16 | 250 |
| 19.44 | 1 | 0 | 1 | 32 | 4 | 8 | 155.52 |
| 18.75 | 1 | 0 | 1 | 32 | 4 | 8 | 150 |
| 15.625 | 1 | 0 | 1 | 32 | 4 | 8 | 125 |
| 15.625 | 1 | 1 | 0 | 32 | 5 | 6.4 | 100 |
| 19.44 | 1 | 1 | 1 | 32 | 8 | 4 | 77.76 |
| 18.75 | 1 | 1 | 1 | 32 | 8 | 4 | 75 |
| 15.625 | 1 | 1 | 1 | 32 | 8 | 4 | 62.5 |

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

| Item | Rating |
|---|--------------------------|
| Supply Voltage, V_{DD} | 4.6V |
| Inputs, V_I | -0.5V to $V_{DD} + 0.5V$ |
| Outputs, I_O Continuous Current Surge Current | 10mA 15mA |
| Package Thermal Impedance, θ_{JA} | 32.1°C/W (0 mps) |
| Storage Temperature, T_{STG} | -65°C to 150°C |

DC Electrical Characteristics

Table 4A. Power Supply DC Characteristics, $V_{DD} = V_{DDA} = V_{DDO_A} = V_{DDO_B} = 3.3V \pm 5\%$, $T_A = 0^\circ C$ to $70^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|---------------------------|-------------------------|-----------------|---------|---------|---------|-------|
| V_{DD} | Positive Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| V_{DDA} | Analog Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| V_{DDO_A}, V_{DDO_B} | Output Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| I_{DD} | Power Supply Current | | | | 135 | mA |
| I_{DDA} | Analog Supply Current | | | | 12 | mA |
| $I_{DDO_A} + I_{DDO_B}$ | Output Supply Current | | | | 80 | mA |

Table 4B. LVCMOS/LVTTL DC Characteristics, $V_{DD} = V_{DDA} = V_{DDO_A} = V_{DDO_B} = 3.3V \pm 5\%$, $T_A = 0^\circ C$ to $70^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|--------------------|---|--------------------------------|---------|----------------|---------|
| V_{IH} | Input High Voltage | | 2 | | $V_{DD} + 0.3$ | V |
| V_{IL} | Input Low Voltage | | -0.3 | | 0.8 | V |
| I_{IH} | Input High Current | REF_CLK, MR, FB_DIV | $V_{DD} = V_{IN} = 3.465V$ | | 150 | μA |
| | | DIV_SELA[0:1], OEA, OEB, DIV_SELB[0:1], VCO_SEL, XTAL_SEL | $V_{DD} = V_{IN} = 3.465V$ | | 5 | μA |
| I_{IL} | Input Low Current | REF_CLK, MR, FB_DIV | $V_{DD} = 3.465V, V_{IN} = 0V$ | -5 | | μA |
| | | DIV_SELA[0:1], OEA, OEB, DIV_SELB[0:1], VCO_SEL, XTAL_SEL | $V_{DD} = 3.465V, V_{IN} = 0V$ | -150 | | μA |

Table 4C. LVDS DC Characteristics, $V_{DD} = V_{DDA} = V_{DDO_A} = V_{DDO_B} = 3.3V \pm 5\%$, $T_A = 0^\circ C$ to $70^\circ C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|-----------------------------|-----------------|---------|---------|---------|-------|
| V_{OD} | Differential Output Voltage | | 250 | | 450 | mV |

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------|---------------------------|-----------------|---------|---------|---------|-------|
| ΔV_{OD} | V_{OD} Magnitude Change | | | | 50 | mV |
| V_{OS} | Offset Voltage | | 1.25 | 1.33 | 1.41 | V |
| ΔV_{OS} | V_{OS} Magnitude Change | | | | 50 | mV |

Table 5. Crystal Characteristics

| Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|------------------------------------|--------------------|-------------|---------|---------|----------|
| Mode of Oscillation | | Fundamental | | | |
| Frequency | FB_DIV = $\div 25$ | 19.6 | | 27.2 | MHz |
| | FB_DIV = $\div 32$ | 15.313 | | 21.25 | MHz |
| Equivalent Series Resistance (ESR) | | | | 50 | Ω |
| Shunt Capacitance | | | | 7 | pF |
| Drive Level | | | | 1 | mW |

AC Electrical Characteristics

Table 6. AC Characteristics, $V_{DD} = V_{DDA} = V_{DDO_A} = V_{DDO_B} = 3.3V \pm 5\%$, $T_A = 0^\circ\text{C}$ to 70°C

| Parameter | Symbol | Test Conditions | Minimum | Typical | Maximum | Units | |
|----------------------|--------------------------------------|------------------------------|---------------------------------|---------|---------|-------|----|
| f_{OUT} | Output Frequency Range | Output Divider = $\div 1$ | 490 | | 680 | MHz | |
| | | Output Divider = $\div 2$ | 245 | | 340 | MHz | |
| | | Output Divider = $\div 3$ | 163.33 | | 226.67 | MHz | |
| | | Output Divider = $\div 4$ | 122.5 | | 170 | MHz | |
| | | Output Divider = $\div 5$ | 98 | | 136 | MHz | |
| | | Output Divider = $\div 8$ | 61.25 | | 85 | MHz | |
| $t_{sk(b)}$ | Bank Skew; NOTE 1 | | | | 33 | ps | |
| $t_{sk(o)}$ | Output Skew | NOTE 2, 3 | Outputs @ Same Frequency | | 75 | ps | |
| | | NOTE 2, 3, 4 | Outputs @ Different Frequencies | | 170 | ps | |
| $f_{jit(\emptyset)}$ | RMS Phase Jitter (Random); NOTE 5 | 625MHz (1.875MHz – 20MHz) | | 0.53 | | ps | |
| | | 312.5MHz (1.875MHz – 20MHz): | | 0.53 | | ps | |
| | | 156.25MHz (1.875MHz – 20MHz) | | 0.56 | | ps | |
| | | 125MHz (1.875MHz – 20MHz) | | 0.58 | | ps | |
| t_R / t_F | Output Rise/Fall Time | | 20% to 80% | | 200 | 450 | ps |
| odc | Output Duty Cycle | | Output Divider $\neq \div 1$ | | 47 | 53 | % |
| | | | Output Divider = $\div 1$ | | 43 | 57 | % |

NOTE 1: Defined as skew within a bank of outputs at the same voltages and with equal load conditions.

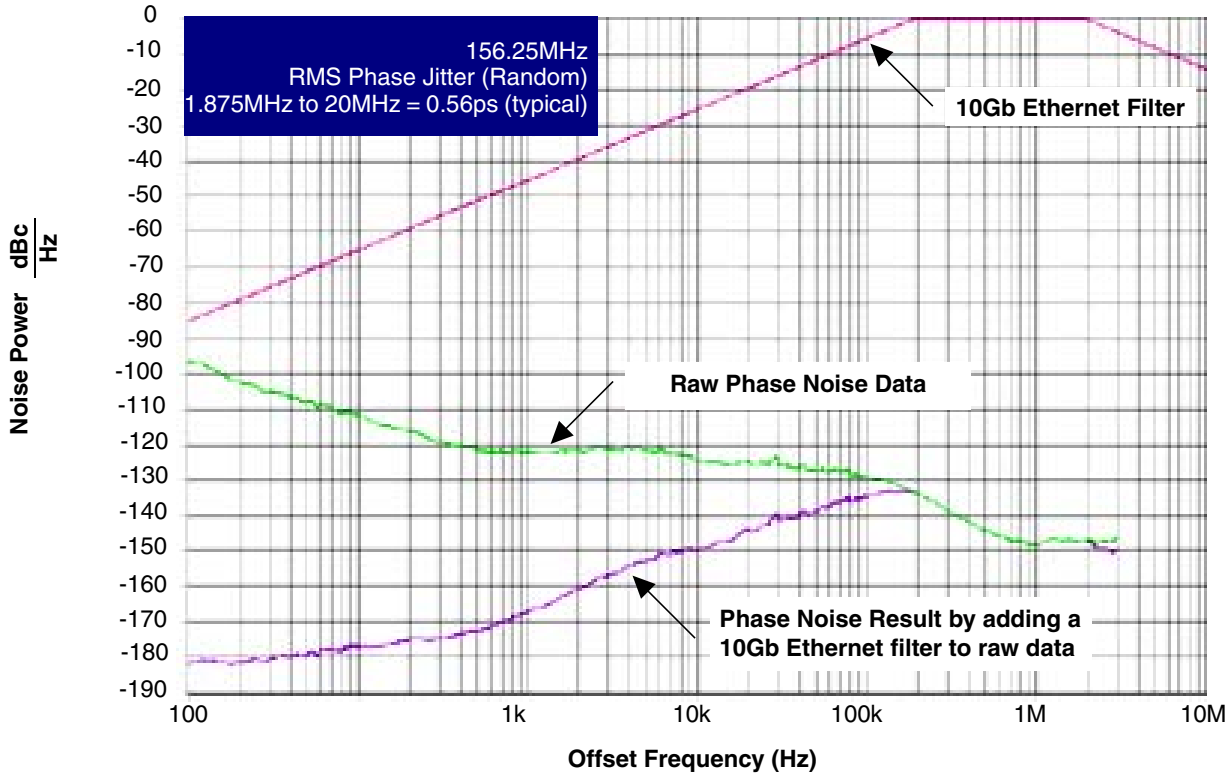
NOTE 2: Defined as skew between outputs at the same supply voltages and with equal load conditions. Measured at the output differential cross points.

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

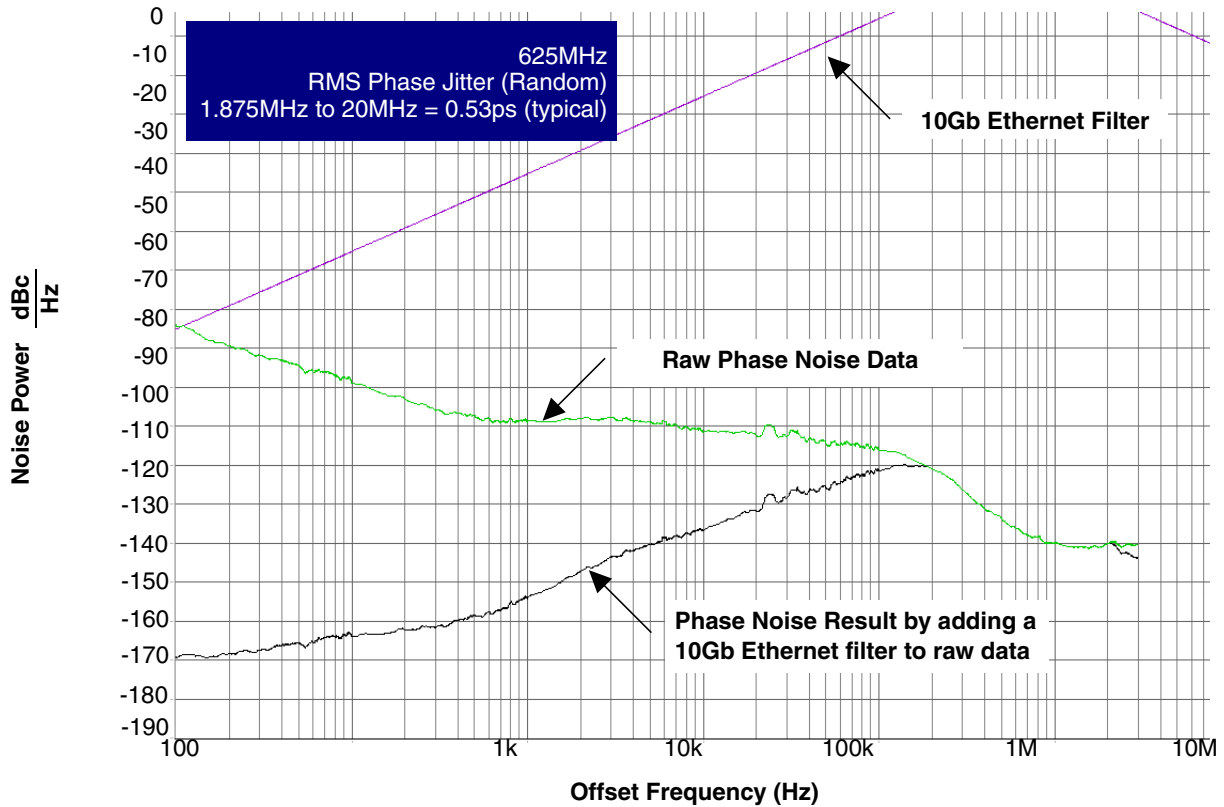
NOTE 4: Characterized using output dividers 1, 2, 4, 8.

NOTE 5: Refer to the Phase Noise Plots.

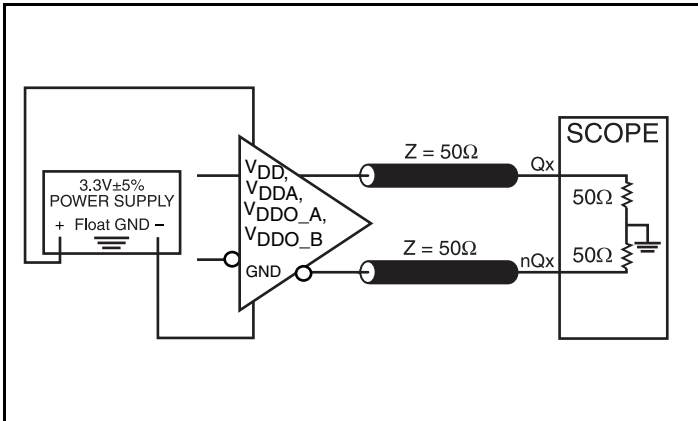
Typical Phase Noise at 156.25MHz



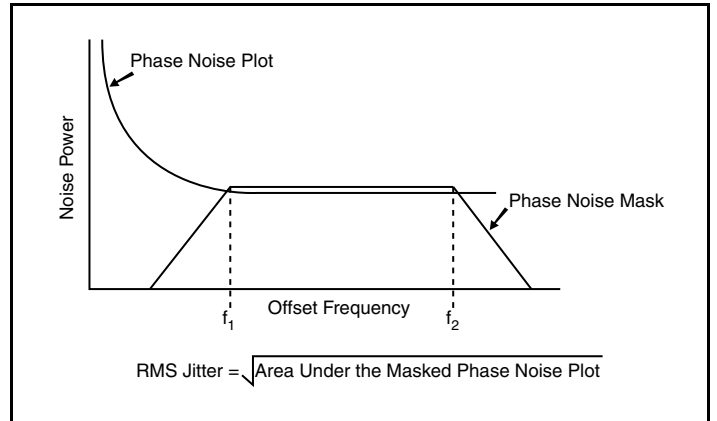
Typical Phase Noise at 625MHz



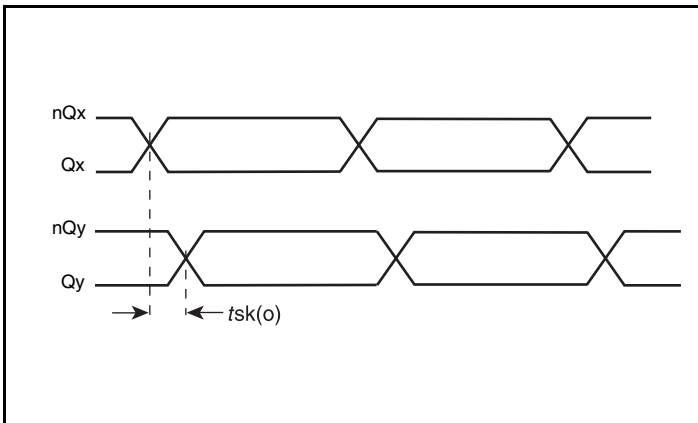
Parameter Measurement Information



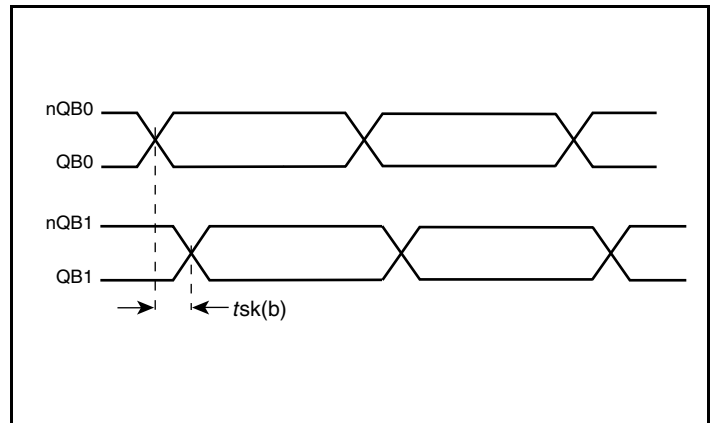
3.3V LVDS Output Load AC Test Circuit



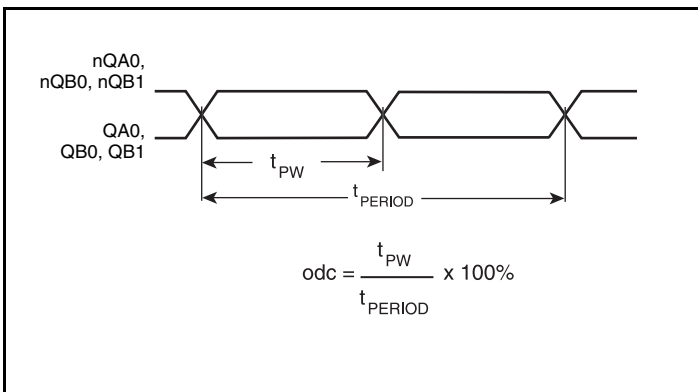
RMS Phase Jitter



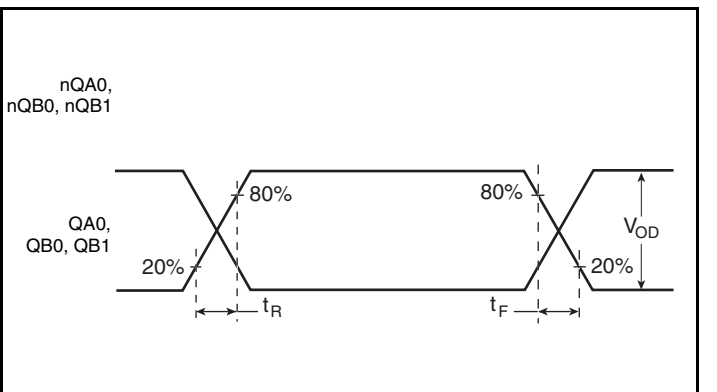
Output Skew



Bank Skew

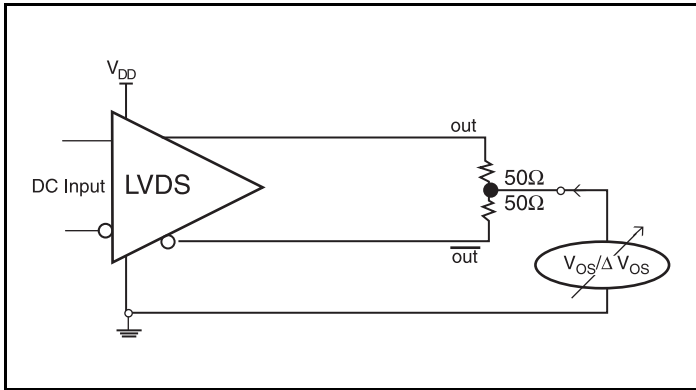


Output Duty Cycle/Pulse Width/Period

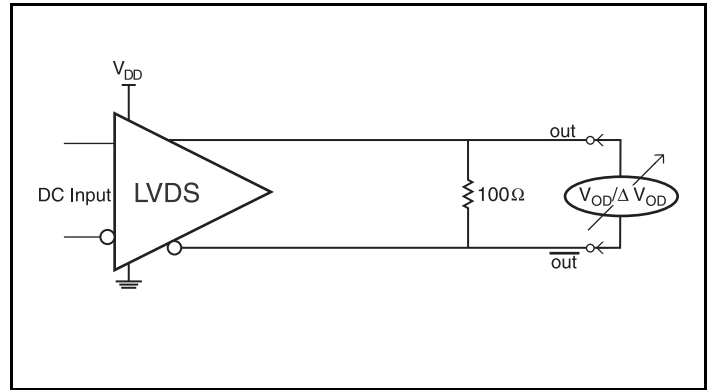


Output Rise/Fall Time

Parameter Measurement Information, continued



Offset Voltage Setup



Differential Output Voltage Setup

Application Information

Power Supply Filtering Technique

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. The 844003-01 provides separate power supplies to isolate any high switching noise from the outputs to the internal PLL. V_{DD} , V_{DDA} , V_{DDO_A} and V_{DDO_B} should be individually connected to the power supply plane through vias, and 0.01μF bypass capacitors should be used for each pin. *Figure 1* illustrates this for a generic V_{DD} pin and also shows that V_{DDA} requires that an additional 10Ω resistor along with a 10μF bypass capacitor be connected to the V_{DDA} pin.

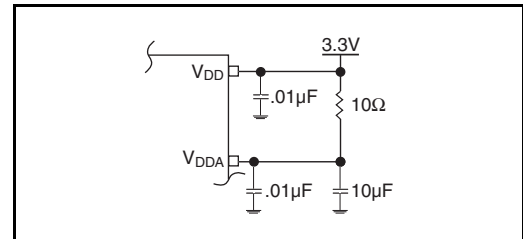


Figure 1. Power Supply Filtering

Crystal Input Interface

The 844003-01 has been characterized with 18pF parallel resonant crystals. The capacitor values shown in *Figure 2* below were

determined using a 19.53125MHz or 25MHz, 18pF parallel resonant crystal and were chosen to minimize the ppm error.

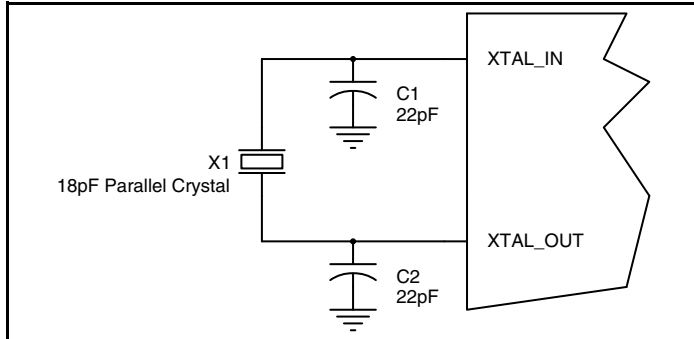


Figure 2. Crystal Input Interface

LVC MOS to XTAL Interface

The XTAL_IN input can accept a single-ended LVC MOS signal through an AC coupling capacitor. A general interface diagram is shown in *Figure 3*. The XTAL_OUT pin can be left floating. The input edge rate can be as slow as 10ns. For LVC MOS signals, it is recommended that the amplitude be reduced from full swing to half swing in order to prevent signal interference with the power rail and to reduce noise. This configuration requires that the output

impedance of the driver (R_o) plus the series resistance (R_s) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This can be done in one of two ways. First, R_1 and R_2 in parallel should equal the transmission line impedance. For most 50Ω applications, R_1 and R_2 can be 100Ω. This can also be accomplished by removing R_1 and making R_2 50Ω.

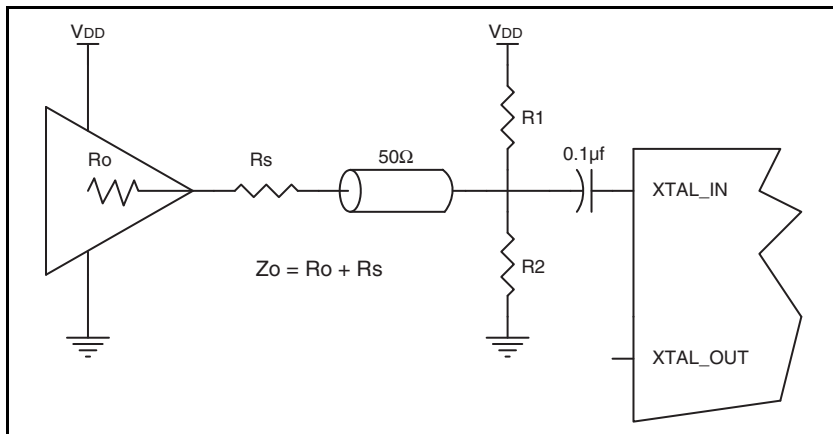


Figure 3. General Diagram for LVC MOS Driver to XTAL Input Interface

Recommendations for Unused Input and Output Pins

Inputs:

Crystal Inputs

For applications not requiring the use of the crystal oscillator input, both XTAL_IN and XTAL_OUT can be left floating. Though not required, but for additional protection, a 1k Ω resistor can be tied from XTAL_IN to ground.

REF_CLK Input

For applications not requiring the use of the reference clock, it can be left floating. Though not required, but for additional protection, a 1k Ω resistor can be tied from the REF_CLK to ground.

LVC MOS Control Pins

All control pins have internal pullups or pulldowns; additional resistance is not required but can be added for additional protection. A 1k Ω resistor can be used.

Outputs:

LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with 100 Ω across. If they are left floating, we recommend that there is no trace attached.

3.3V LVDS Driver Termination

A general LVDS interface is shown in *Figure 4*. In a 100 Ω differential transmission line environment, LVDS drivers require a matched load termination of 100 Ω across near the receiver input. For a multiple

LVDS outputs buffer, if only partial outputs are used, it is recommended to terminate the unused outputs.

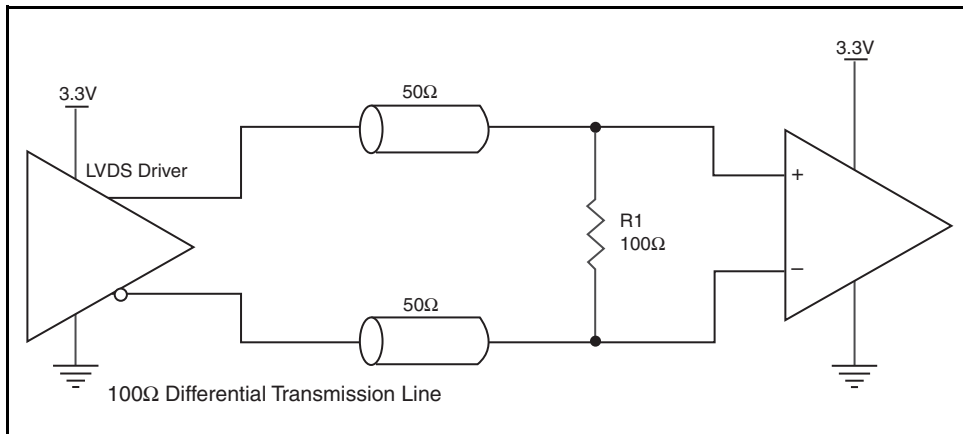


Figure 4. Typical LVDS Driver Termination

EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 5*. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as “heat pipes”. The number of vias (i.e. “heat pipes”) are application specific

and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, refer to the Application Note on the *Surface Mount Assembly* of Amkor’s Thermally/Electrically Enhance Leadframe Base Package, Amkor Technology.

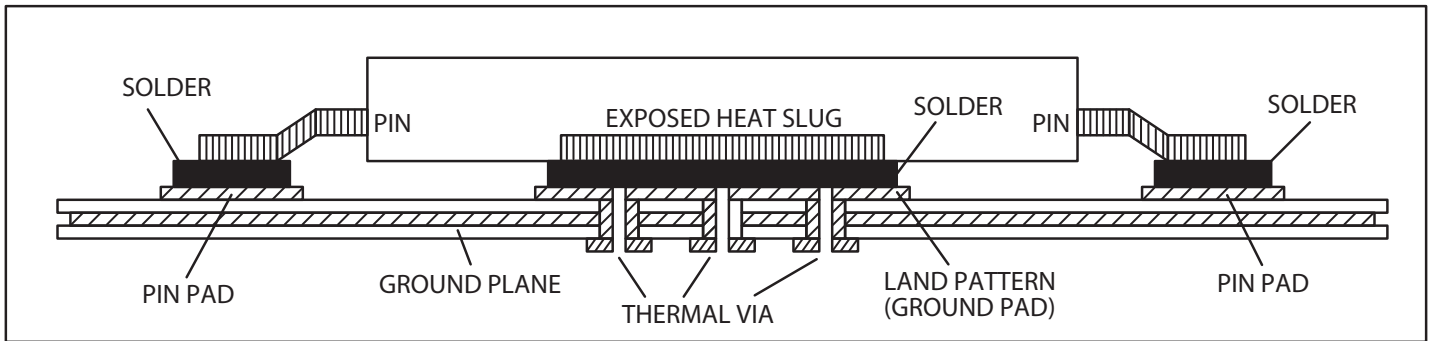


Figure 5. Assembly for Exposed Pad Thermal Release Path - Side View (drawing not to scale)

Power Considerations

This section provides information on power dissipation and junction temperature for the 844003-01. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the 844003-01 is the sum of the core power plus the analog power plus the power dissipated in the load(s). The following is the power dissipation for $V_{DD} = 3.3V + 5\% = 3.465V$, which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)_{MAX} = $V_{DD_MAX} * (I_{DD_MAX} + I_{DDA_MAX}) = 3.465V * (135mA + 12mA) = \mathbf{509.36mW}$
- Power (outputs)_{MAX} = $V_{DDO_MAX} * I_{DDO_MAX} = 3.465V * 80mA = \mathbf{277.20mW}$

Total Power_{MAX} = $509.36mW + 277.20mW = \mathbf{786.56mW}$

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad and directly affects the reliability of the device. The maximum recommended junction temperature for HiPerClockS devices is 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 32.1°C/W per Table 7 below.

Therefore, T_j for an ambient temperature of 70°C with all outputs switching is:

$$70^\circ\text{C} + 0.787\text{W} * 32.1^\circ\text{C/W} = 95.3^\circ\text{C}. \text{ This is below the limit of } 125^\circ\text{C}.$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board.

Table 7. Thermal Resistance θ_{JA} for 24 Lead TSSOP, E-Pad, Forced Convection

| Meters per Second | θ_{JA} by Velocity | | |
|---|---------------------------|----------|----------|
| | 0 | 1 | 2 |
| Multi-Layer PCB, JEDEC Standard Test Boards | 32.1°C/W | 35.5°C/W | 26.9°C/W |

Reliability Information

Table 8. θ_{JA} vs. Air Flow Table for a 24 Lead TSSOP, E-Pad

| θ_{JA} by Velocity | | | |
|---|----------|----------|----------|
| Meters per Second | 0 | 1 | 2 |
| Multi-Layer PCB, JEDEC Standard Test Boards | 32.1°C/W | 35.5°C/W | 26.9°C/W |

Transistor Count

The transistor count for 844003-01 is: 3537

Package Outline and Package Dimensions

Package Outline - G Suffix for 24 Lead TSSOP, E-Pad

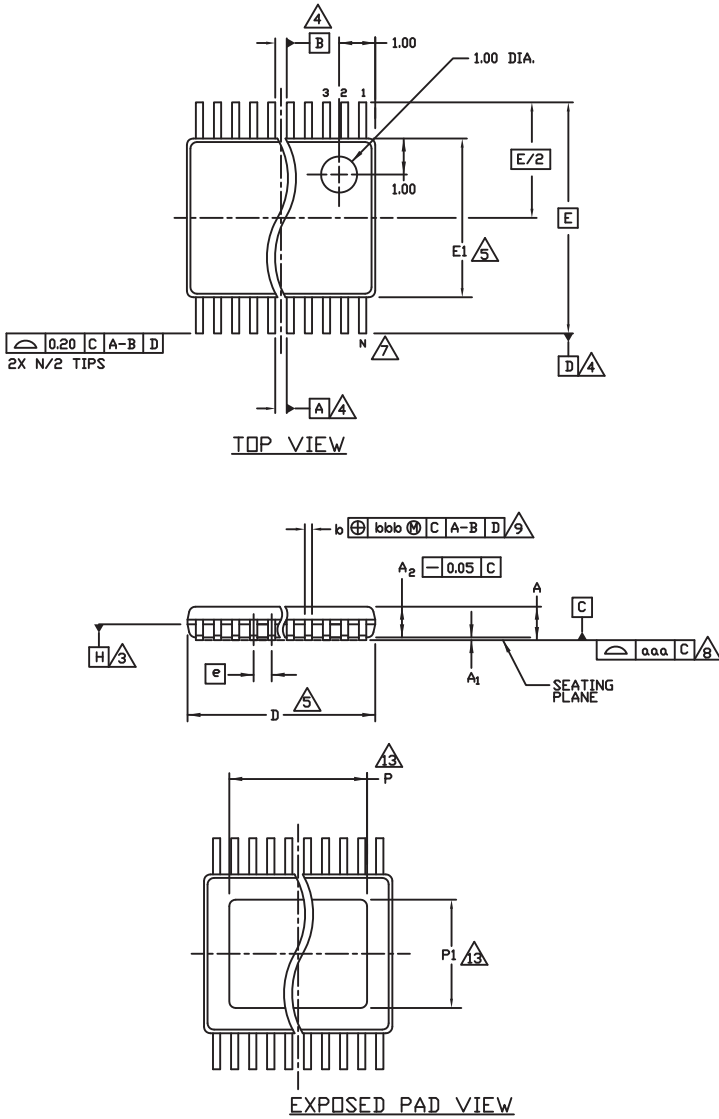
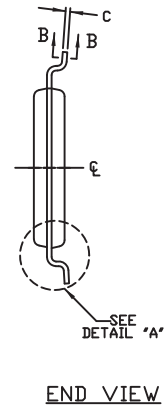
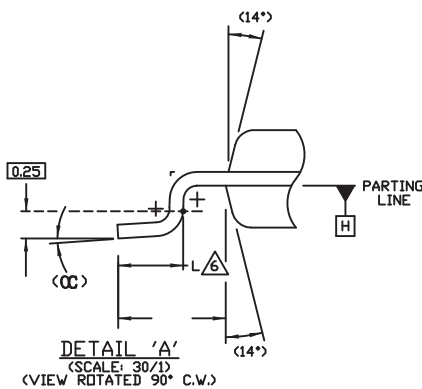
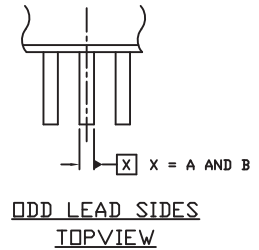
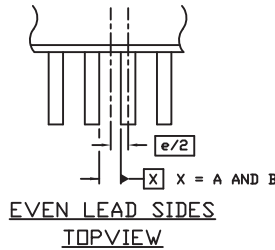


Table 9. Package Dimensions

| All Dimensions in Millimeters | | | |
|-------------------------------|------------|---------|---------|
| Symbol | Minimum | Nominal | Maximum |
| N | 24 | | |
| A | | | 1.10 |
| A1 | 0.05 | | 0.15 |
| A2 | 0.85 | 0.90 | 0.95 |
| b | 0.19 | | 0.30 |
| b1 | 0.19 | 0.22 | 0.25 |
| c | 0.09 | | 0.20 |
| c1 | 0.09 | 0.127 | 0.16 |
| D | 7.70 | | 7.90 |
| E | 6.40 Basic | | |
| E1 | 4.30 | 4.40 | 4.50 |
| e | 0.65 Basic | | |
| L | 0.50 | 0.60 | 0.70 |
| P | 5.0 | | 5.5 |
| P1 | 3.0 | | 3.2 |
| α | 0° | | 8° |
| $\alpha\alpha\alpha$ | 0.076 | | |
| bbb | 0.10 | | |



SECTION "B-B"
 SCALE: 120/1
 (SEE NOTE 10)
SIDE VIEW

Ordering Information

Table 10. Ordering Information

| Part/Order Number | Marking | Package | Shipping Packaging | Temperature |
|-------------------|---------------|----------------------------------|--------------------|-------------|
| 844003BG-01LF | ICS844003B01L | “Lead-Free” 24 Lead TSSOP, E-Pad | Tube | 0°C to 70°C |
| 844003BG-01LFT | ICS844003B01L | “Lead-Free” 24 Lead TSSOP, E-Pad | Tape & Reel | 0°C to 70°C |

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

Revision History Sheet

| Rev | Table | Page | Description of Change | Date |
|-----|-------|---------|--|---------|
| A | T10 | 1 18 | Features section - removed bullet referencing leaded devices Ordering Information - removed leaded devices. Updated data sheet format. | 6/10/15 |
| | | | | |
| | | | | |
| | | | | |

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